

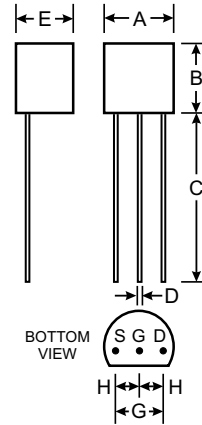
P-CHANNEL ENHANCEMENT MODE DMOS TRANSISTOR

Features

- High Breakdown Voltage
- High Input Impedance
- Fast Switching Speed
- Low Drain-Source On-Resistance
- Specially Suited for Telephone Subsets

Mechanical Data

- Case: TO-92, Plastic
- Leads: Solderable per MIL-STD-202, Method 208
- Pin Connections: See Diagram
- Weight: 0.18 grams (approx.)



TO-92		
Dim	Min	Max
A	4.45	4.70
B	4.46	4.70
C	12.7	—
D	0.41	0.63
E	3.43	3.68
G	2.42	2.67
H	1.14	1.40
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain-Source-Voltage	$-V_{bss}$	240	V
Drain-Gate-Voltage	$-V_{DGS}$	200	V
Gate-Source-Voltage (pulsed) (Note 2)	V_{GS}	± 20	V
Drain-Current (continuous)	$-I_D$	200	mA
Power Dissipation @ $T_C = 25^\circ\text{C}$ (Note 1)	P_d	830	mW
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

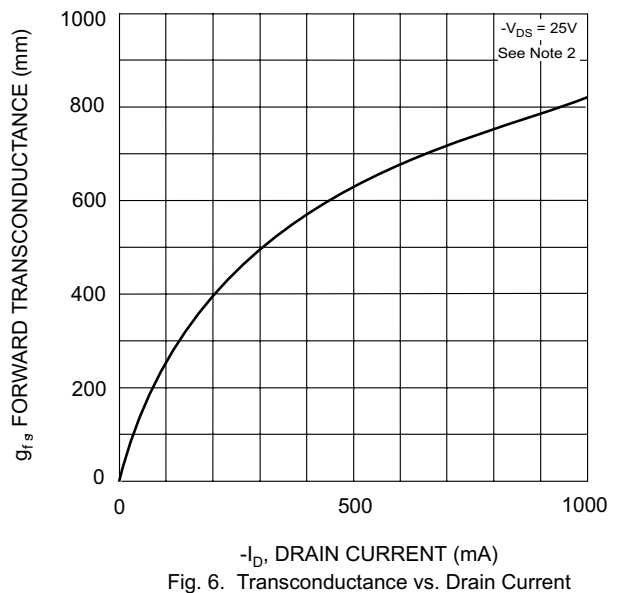
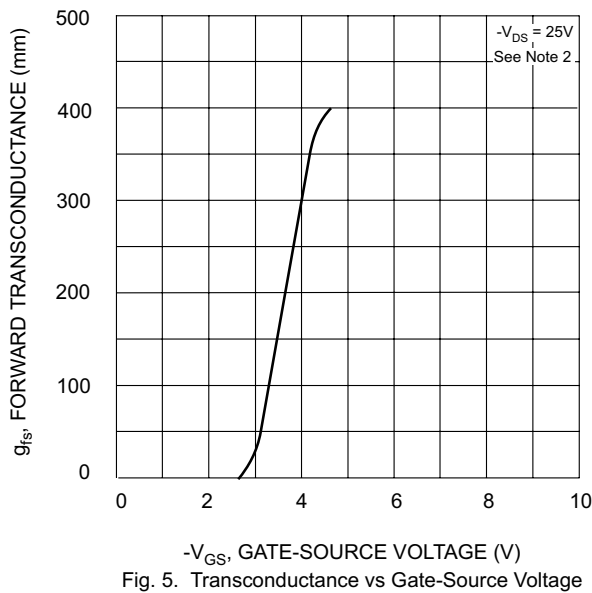
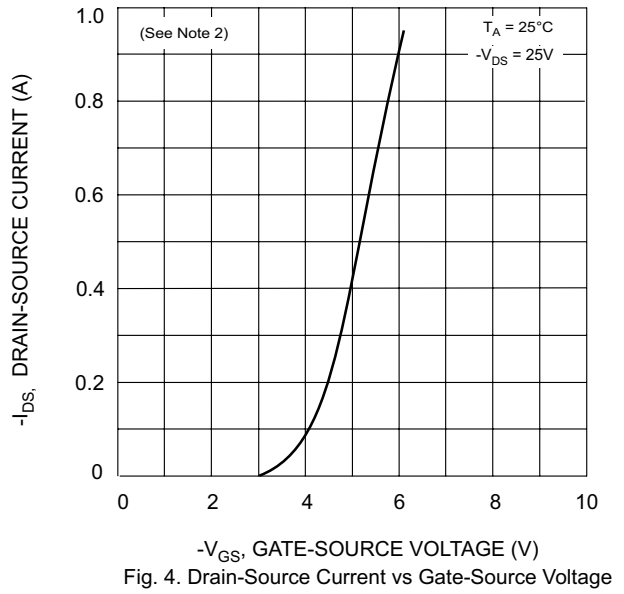
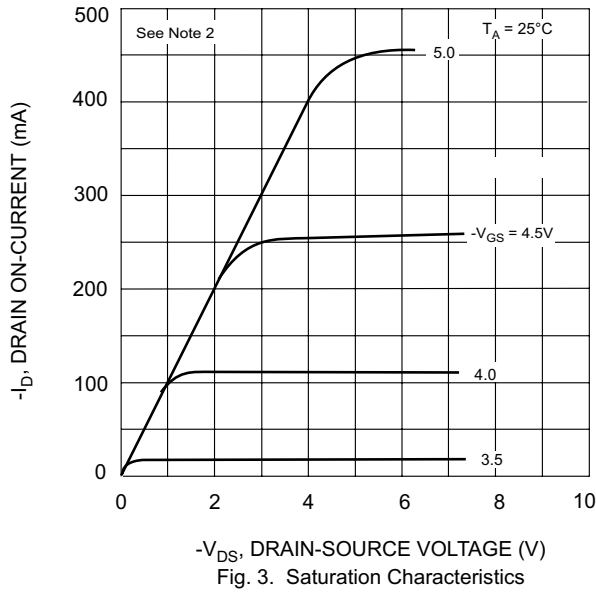
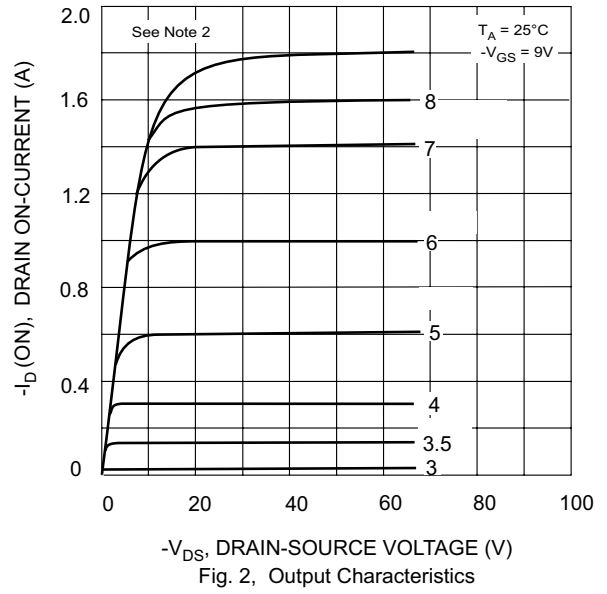
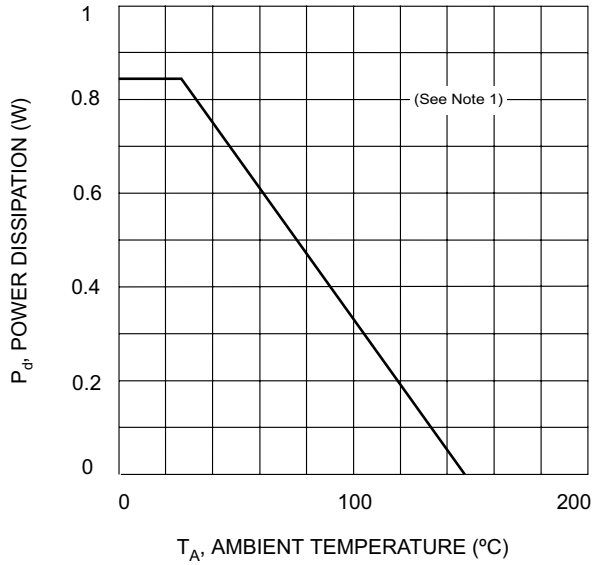
Inverse Diode @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Maximum Forward Current (continuous)	I_F	0.22	A
Forward Voltage Drop (Typical) @ $V_{GS} = 0, I_F = 0.75\text{A}, T_j = 25^\circ\text{C}$	V_F	0.85	V

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Drain-Source Breakdown Voltage	$-V_{(BR)DSS}$	200	230	—	V	$-I_D = 100\mu\text{A}, V_{GS} = 0$
Gate-Body Leakage Current	$-I_{GSS}$	—	—	10	nA	$-V_{GS} = 15\text{V}, V_{DS} = 0$
Drain-Source Cutoff Current	$-I_{DSS}$ $-I_{DSX}$	—	—	1.0 25	μA	$-V_{DS} = 130\text{V}, V_{GS} = 0$ $-V_{DS} = 10\text{V}, -V_{GS} = 0.2\text{V}$
Gate-Source Threshold Voltage	$-V_{GS(th)}$	—	2.8	4.0	V	$V_{GS} = V_{DS}, -I_D = 1.0\text{mA}$
Drain-Source ON Resistance	$r_{DS(ON)}$	—	7.0	14	Ω	$-V_{GS} = 10\text{V}, -I_D = 100\text{mA}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	—	—	150	K/W	Note 1
Input Capacitance	C_{iss}	—	270	—	pF	$-V_{DS} = 20\text{V}, V_{GS} = 0, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	35	—	pF	
Feedback Capacitance	C_{rss}	—	6.0	—	pF	

- Notes:
1. Valid provided that leads are kept at ambient temperature at a distance of 2.0mm from case.
 2. Pulse Test: Pulse width = 80 μs , duty factor = 1%.



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